## PATENT ABSTRACTS OF JAPAN

(11)Publication number:

2001-189312

(43)Date of publication of application: 10.07.2001

(51)Int.CI.

H01L 21/316 C30B 29/16 H01L 27/105 H01L 27/108 H01L 21/8242 H01L 29/78 H01L 21/8247 H01L 29/788 H01L 29/792

(21)Application number: 2000-322458

(71)Applicant: MOTOROLA INC

(22)Date of filing:

23.10.2000

(72)Inventor: RAMDANI JAMAL

DROOPAD RAVINDRANATH

YU ZHIYI JIMMY

(30)Priority

Priority number: 1999 425945

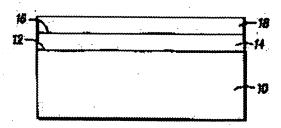
Priority date: 25.10.1999

Priority country: US

## (54) METHOD OF MANUFACTURING SEMICONDUCTOR STRUCTURE HAVING METAL OXIDE INTERFACE WITH SILICON

## (57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of manufacturing semiconductor structure with which a thin stable silicide interface with silicon can be manufactured. SOLUTION: This method of manufacturing semiconductor structure comprises a step of providing a silicon substrate 10 having a surface 12, a step of forming seed layers 20 and 20' composed of silicide materials on the surface 12 of the substrate 10 by atomic layer deposition(ALD), and a step of forming one or more layers of an oxide 40 having a high dielectric constant on the seed layers 20 and 20' by atomic layer deposition(ALD).



## **LEGAL STATUS**

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]